

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 6074917 A	8	LPCVD oxide and RTA for top oxide of ONO film to improve reliability for flash memory devices	438/261	257/E29.129; 257/E29.165; 438/786; 438/954	Chang, Kent Kuohua et al.
2	US 6376341 B1	8	Optimization of thermal cycle for the formation of pocket implants	438/510	438/257; 438/258; 438/266	Kluth, George J. et al.
3	US 6306777 B1	9	Flash memory having a treatment layer disposed between an interpoly dielectric structure and method of forming	438/763	257/639; 257/640; 257/646; 257/649; 438/758; 438/761; 438/787; 438/791	Ogle, Jr., Robert B. et al.